

NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE7190A uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications.

General Features

• $V_{DS} = 71V, I_D = 90A$ $R_{DS(ON)} < 5.5 \text{ m}\Omega @ V_{GS} = 10V$ (Typ:4.8m Ω)

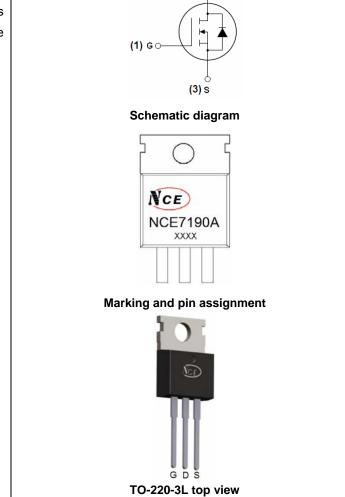
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Special designed for convertors and power controls
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- Power switching application
- Hard switched and High frequency circuits
- Uninterruptible power supply

100% UIS TESTED!

100% ΔVds TESTED!



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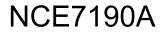
Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE7190A	NCE7190A	TO-220-3L	-	-	-

Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	VDS	71	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	I _D	90	Α
Drain Current-Continuous(T _C =100 ℃)	I _D (100℃)	63	А
Pulsed Drain Current	I _{DM}	320	А
Maximum Power Dissipation	PD	170	W
Derating factor		1.13	W/°C
Single pulse avalanche energy (Note 5)	E _{AS}	812	mJ
Operating Junction and Storage Temperature Range	TJ,TSTG	-55 To 175	°C





Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	R _{θJC}	0.88	°C/W	1
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Electrical Characteristics (T_A=25[°]C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics			•			
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	71	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =71V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)	·		•			
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250µA	2	2.85	4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =20A	-	4.8	5.5	mΩ
Forward Transconductance	g fs	V _{DS} =5V,I _D =20A	-	50	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}		-	4900	-	PF
Output Capacitance	Coss	V_{DS} =25V, V_{GS} =0V,	-	380	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	-	290	-	PF
Switching Characteristics (Note 4)			•			
Turn-on Delay Time	t _{d(on)}		-	17	-	nS
Turn-on Rise Time	tr	VDD=35V,RL=15Ω	-	11	-	nS
Turn-Off Delay Time	t _{d(off)}	RG=2.5Ω,VGS=10V	-	55	-	nS
Turn-Off Fall Time	t _f		-	15	-	nS
Total Gate Charge	Qg)/ OF)// OOA	-	100	-	nC
Gate-Source Charge	Q _{gs}	V_{DS} =35V,I _D =20A,	-	21	-	nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	30	-	nC
Drain-Source Diode Characteristics	·		•			
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =20A	-	-	1.2	V
Diode Forward Current (Note 2)	ls		-	-	90	Α
Reverse Recovery Time	t _{rr}	Tj=25℃,I _F =100A	-		37	nS
Reverse Recovery Charge	Qrr	di/dt=100A/µs ^(Note3)	-		58	nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD				

Notes:

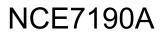
1. Repetitive Rating: Pulse width limited by maximum junction temperature.

- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- **3.** Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production



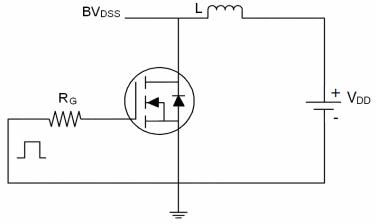
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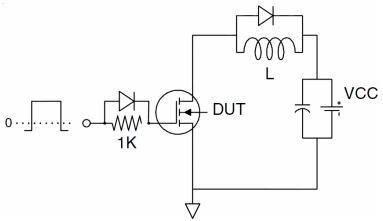


Test Circuit

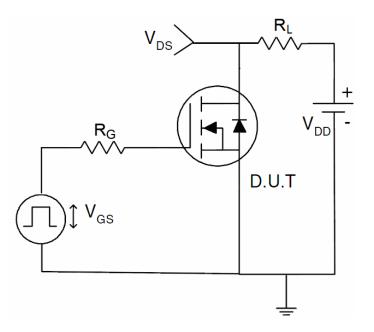
1) E_{AS} Test Circuits



2) Gate Charge Test Circuit

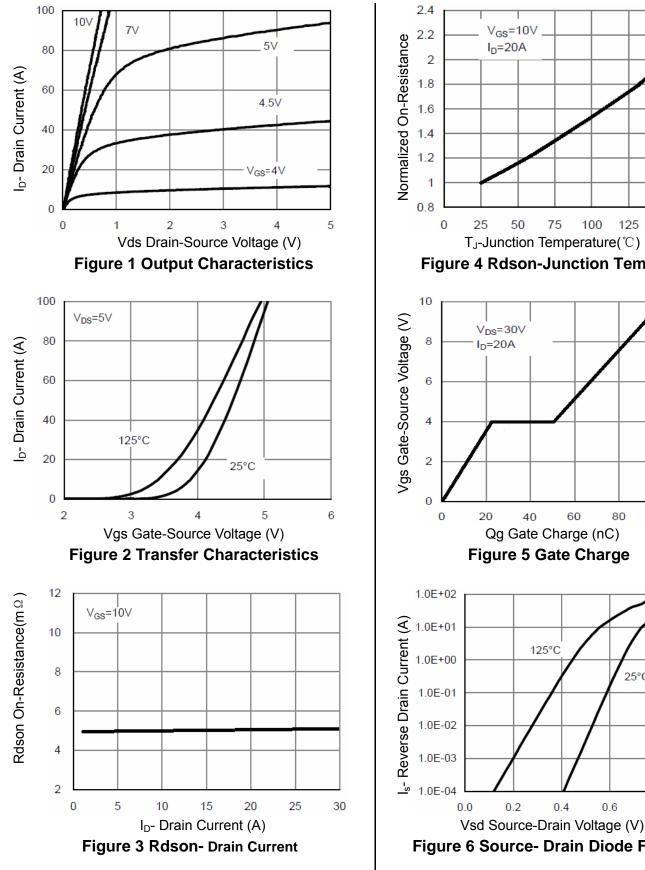


3) Switch Time Test Circuit





Typical Electrical and Thermal Characteristics (Curves)



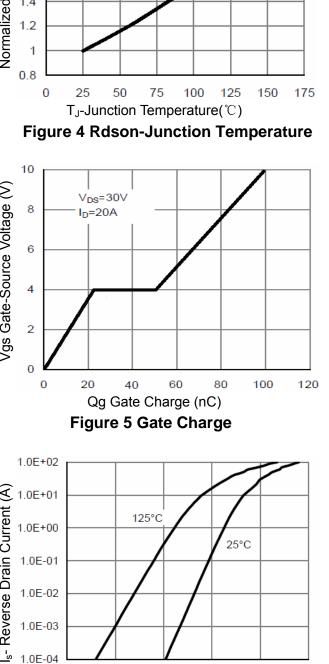


Figure 6 Source- Drain Diode Forward

0.4

0.6

0.8

1.0



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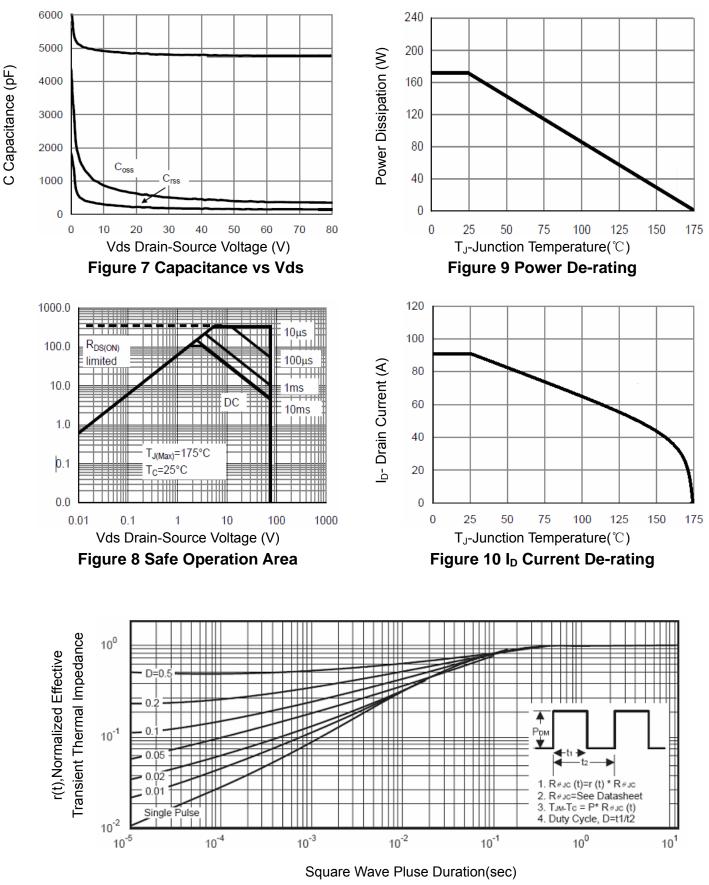


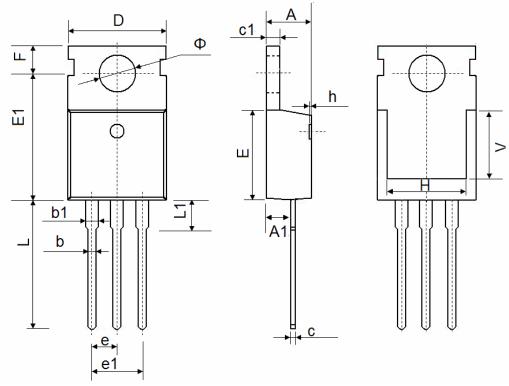
Figure 11 Normalized Maximum Transient Thermal Impedance



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TO-220-3L Package Information



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
A	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
с	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
E	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.54	TYP.	0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	7.500) REF.	0.295 REF.		
Φ	3.400	3.800	0.134	0.150	





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